

Electronic Supporting Information (ESI)

A highly efficient transition metal oxide layer for hole extraction and transport in inverted polymer bulk heterojunction solar cells

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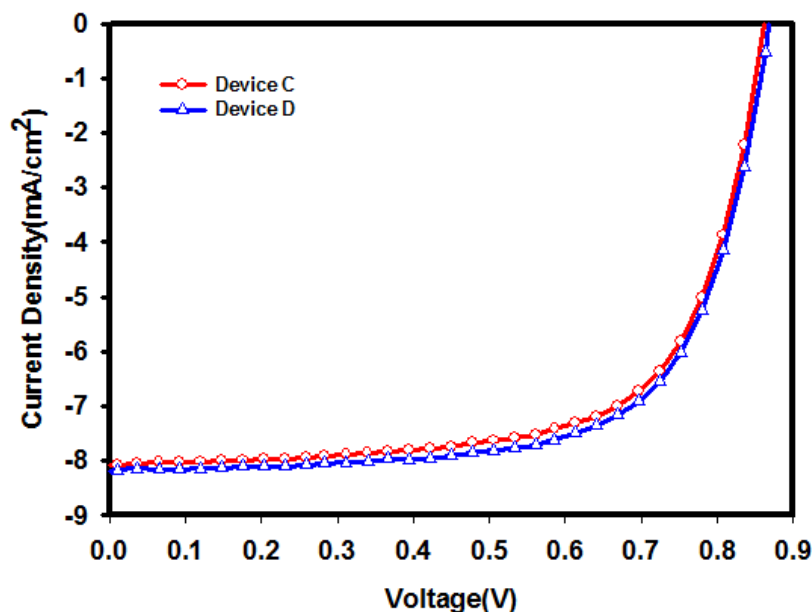


Fig. S1 Current Density versus Voltage characteristics for the following devices:

Device C: Glass/ITO/ZnO(~30nm)/P3HT:ICBA(~80nm)/MoO₃(10nm)/Al(100nm);

Device D: Glass/ITO/ZnO(~30nm)/P3HT:ICBA (~80nm)/WO₃ (5nm)/Al (100nm)

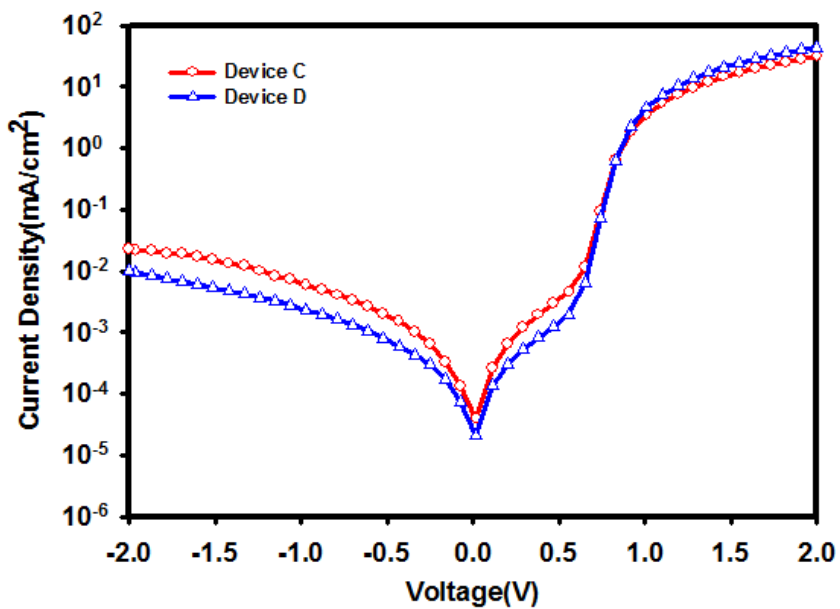


Fig. S2 Current Density versus Voltage characteristics for Device C and Device D

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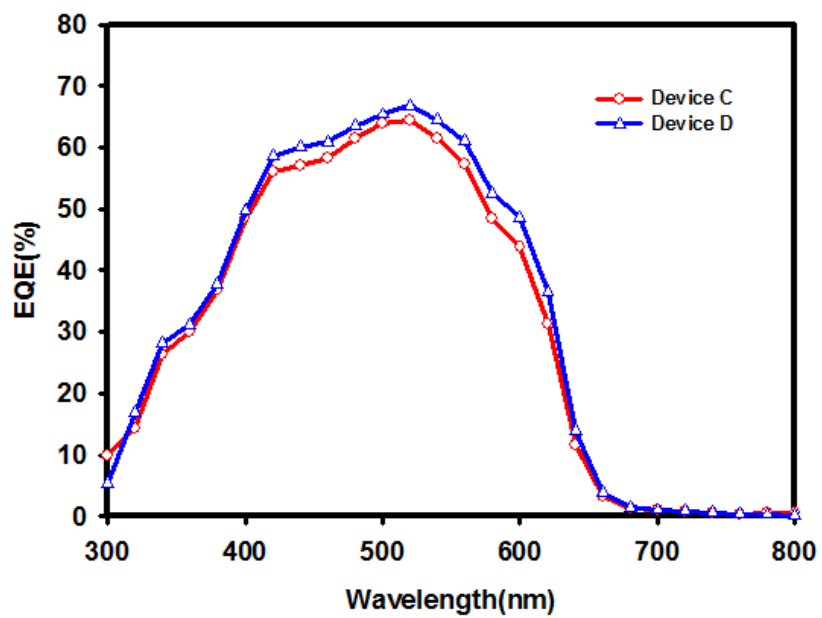


Fig. S3 EQE spectrum of Device C and Device D

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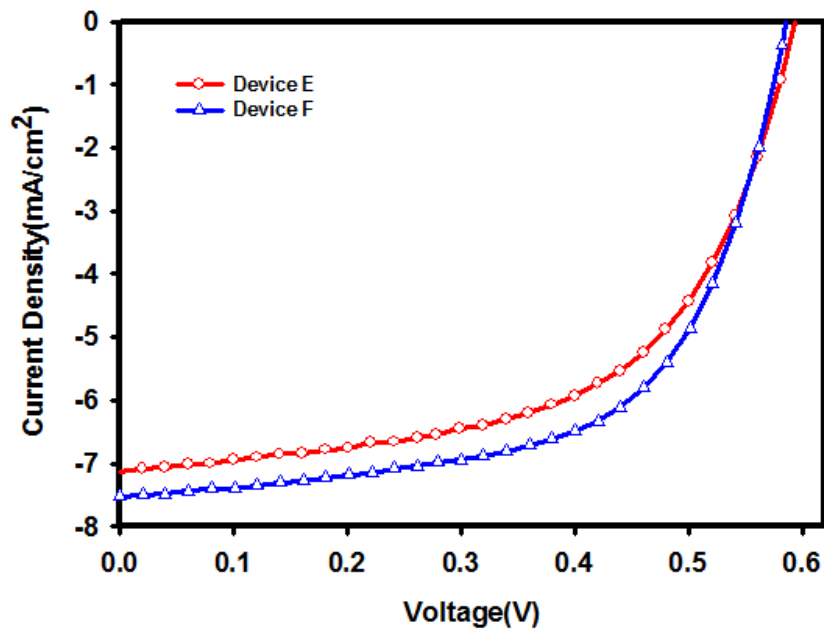


Fig. S4 Current Density vs. Voltage characteristics of the following devices:

Device E: Glass/ITO/ZnO(~30nm)/P3HT:PCBM(~120nm)/MoO₃(10nm)/Al(100nm);

Device F: Glass/ITO/ZnO(~30nm)/P3HT:PCBM (~120nm)/WO₃ (5nm)/Al (100nm)

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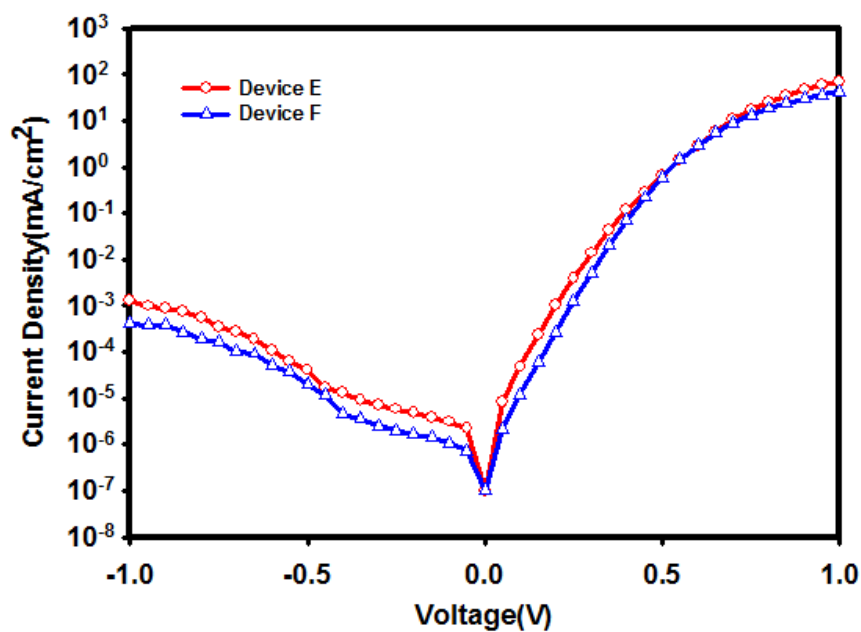


Fig. S5 Dark Current Density vs. Voltage characteristics of Device E and Device F